

Description

The AU4521P4-3 is a high power TVS, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive lines. The AU4521P4-3 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a 3-pin DFN2020-3 lead-free package. The leads are finished with NiPdAu. Each device will protect one line. The combination of small size, and high surge capability makes them ideal for use in applications such as cellular phones, LCD displays, USB, and multi media card interfaces.

Features

6000W peak pulse power (8/20µs)

Low leakage: nA levelOperating voltage: 4.5V

• Ultra low clamping voltage

• One power line protects

• Complies with following standards:

IEC 61000-4-2 (ESD) immunity test
Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 300A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: DFN2020-3Lead Finish: NiPdAu

Case Material: "Green" Molding CompoundMoisture Sensitivity: Level 3 per J-STD-020

Terminal Connections: See Diagram Below

Marking Information: See Below

Applications

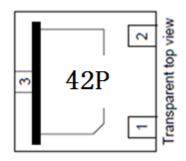
Power Management

• Industrial Application

Power Supply Protection

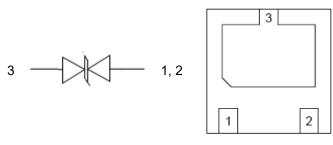
Notebooks, desktops, and servers

Marking Information



42P:Deavice Marking Code Bar denotes cathode

Dimensions and Pin Configuration



Transparent top view

Circuit Diagram

Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU4521P4-3	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

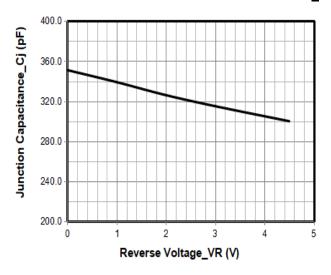
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	6000	W
Peak Pulse Current (8/20µs)	IPP	300	А
ESD per IEC 61000-4-2 (Air)	Vesd	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	N.V
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

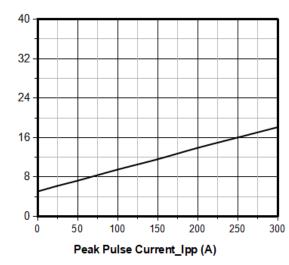
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			4.5	V	
Breakdown Voltage	VBR	4.8			V	IT = 1mA
Reverse Leakage Current	I _R			1.0	μA	VRWM = 4.5V
Clamping Voltage	Vc			8.5	V	IPP = 50A (8 x 20µs pulse)
Clamping Voltage	Vc			20	V	IPP = 300A (8 x 20µs pulse)
Junction Capacitance	Cı		350		pF	VR = 0V, f = 1MHz



Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

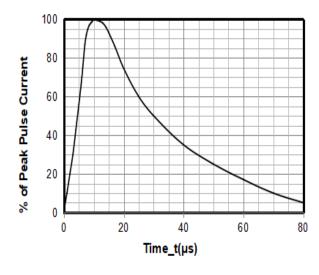


Junction Capacitance vs. Reverse Voltage

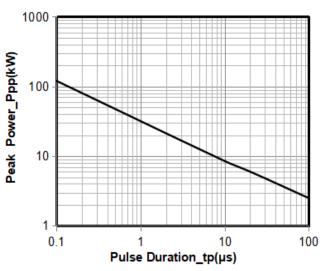


Clamping Voltage _Vc(V)

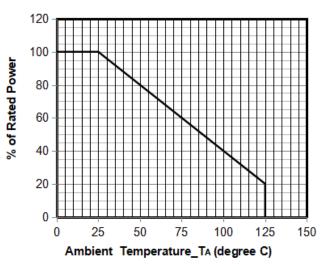
Clamping Voltage vs. Peak Pulse Current



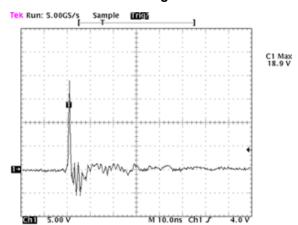
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



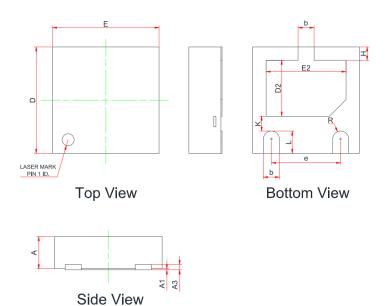
Power Derating Curve



Note: Data is taken with a 10x attenuator **ESD Clamping Voltage** 8 kV Contact per IEC61000-4-2

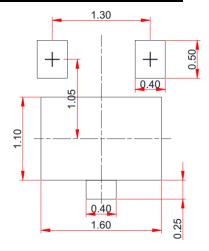


DFN2020-3 Package Outline Drawing



	MILLIMETERS				
SYM	MIN	NOM	MAX		
Α	0.55	0.60	0.65		
A1	0.00	0.02	0.05		
A3	0.10REF.				
b	0.25		0.35		
D	1.90		2.10		
Е	1.90		2.10		
D2	0.95		1.15		
E2	1.40		1.60		
е	1.20		1.40		
Н	0.20		0.30		
K	0.20		0.40		
L	0.35		0.45		
R	0.13				

Suggested Land Pattern



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